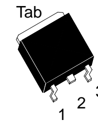
H3055MJ

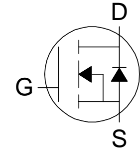
N-Channel Enhancement-Mode MOSFET (30V, 12A)

H3055MJ Pin Assignment



3-Lead Plastic **TO-252**
Package Code: J
Pin 1: Gate
Pin 2 & Tab: Drain
Pin 3: Source

Internal Schematic Diagram



Description

This N-Channel 2.5V specified MOSFET is a rugged gate version of advanced trench process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5V-10V)

Features

- $R_{DS(on)}$=45mΩ@V_{GS}=4.5V, I_D=5.2A; $R_{DS(on)}$=35mΩ@V_{GS}=10V, I_D=6A
- High Density Cell Design for Ultra Low On-Resistance
- High Power and Current Handing Capability
- Fully Characterized Avalanche Voltage and Current
- Ideal for Li ion Battery Pack Applications

Applications

- Battery Protection
- Load Switch
- Power Management

Absolute Maximum Ratings (T_A=25°C, unless otherwise noted)

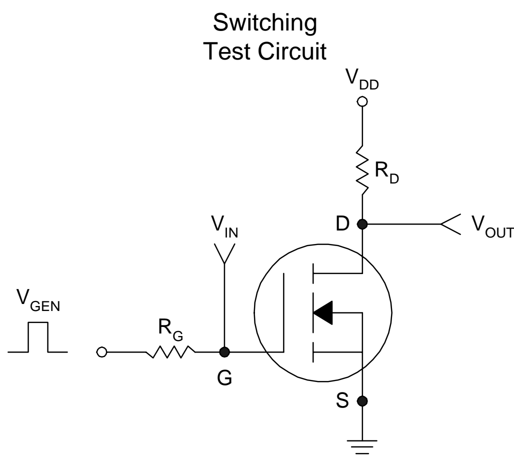
Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current (Continuous)	12	A
I_{DM}	Drain Current (Pulsed) *1	30	A
P_D	Total Power Dissipation @T_A=25°C	2	W
	Total Power Dissipation @T_A=75°C	1.3	W
T_j, T_{stg}	Operating and Storage Temperature Range	-55 to +150	°C
$R_{\theta JA}$	Thermal Resistance Junction to Ambient *2	62.5	°C/W

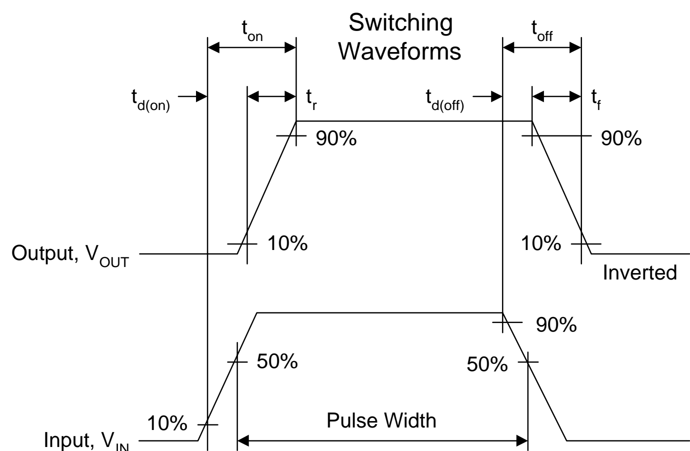
*1: Maximum DC current limited by the package
*2: 1-in^2 2oz Cu PCB board

Electrical Characteristics (T_A=25°C, unless otherwise noted)

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
• Static						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	30	-	-	V
$R_{DS(on)}$	Drain-Source On-State Resistance	V_{GS}=4.5V, I_D=5.2A	-	34	45	mΩ
		V_{GS}=10V, I_D=6A	-	25	35	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	0.6	-	1.5	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V	-	-	1	uA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
g_{FS}	Forward Transconductance	V_{DS}=10V, I_D=6A	7	13	-	S
• Dynamic						
Q_g	Total Gate Charge	V_{DS}=10V, I_D=6A, V_{GS}=6.9V	-	4.2	-	nC
Q_{gs}	Gate-Source Charge		-	1.2	-	
Q_{gd}	Gate-Drain Charge		-	1.7	-	
C_{iss}	Input Capacitance	V_{DS}=10V, V_{GS}=0V, f=1MHz	-	410	-	pF
C_{oss}	Output Capacitance		-	73	-	
C_{rss}	Reverse Transfer Capacitance		-	55	-	
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=15V, I_D=1A, V_{GEN}=10V R_{GEN}=3Ω, R_L=2.2Ω	-	3	-	ns
t_r	Turn-on Rise Time		-	2	-	
$t_{d(off)}$	Turn-off Delay Time		-	10	-	
t_f	Turn-off Fall Time		-	3	-	
• Drain-Source Diode Characteristics						
I_S	Maximum Diode Forward Current		-	-	4.3	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS}=0V, I_S=1A	-	-	1	V

Note: Pulse Test: Pulse Width ≤300us, Duty Cycle≤2%





TO-252 Dimension

3-Lead TO-252 Plastic
Surface Mount Package
HSMC Package Code: J

Marking:

Pb Free Mark
Pb-Free: "•" (Note)
Normal: None

H J
3 0 5 5 M

Date Code
Control Code

Note: Green label is used for pb-free packing

Pin Style: 1.Gate 2.Drain 3.Source

Material:
- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	6.35	6.80
C	4.80	5.50
F	1.30	1.70
G	5.40	6.25
H	2.20	3.00
L	0.40	0.90
M	2.20	2.40
N	0.90	1.50
a1	0.40	0.65
a2	-	*2.30
a5	0.65	1.05

*: Typical, Unit: mm

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- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	6.40	6.80
B	-	6.00
C	5.04	5.64
D	-	*4.34
E	0.40	0.80
F	0.50	0.90
G	5.90	6.30
H	2.50	2.90
I	9.20	9.80
J	0.60	1.00
K	-	0.96
L	0.66	0.86
M	2.20	2.40
N	0.70	1.10
O	0.82	1.22
a1	0.40	0.60
a2	2.10	2.50
y1	-	5°
y2	-	3°

*: Typical, Unit: mm

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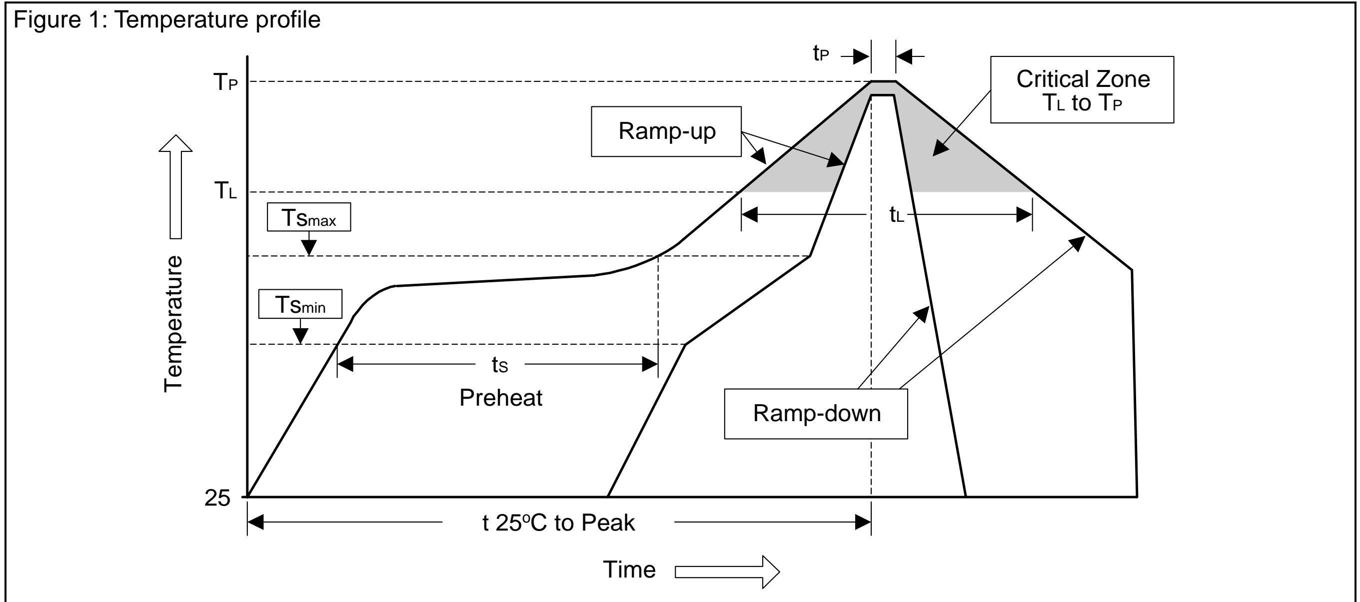
Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%

2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat - Temperature Min (Ts_{min}) - Temperature Max (Ts_{max}) - Time (min to max) (ts)	 100°C 150°C 60~120 sec	 150°C 200°C 60~180 sec
Tsmax to T_L - Ramp-up Rate	 <3°C/sec	 <3°C/sec
Time maintained above: - Temperature (T_L) - Time (t_L)	 183°C 60~150 sec	 217°C 60~150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	10sec ±1sec
Pb-Free devices.	260°C ±5°C	10sec ±1sec